

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Previously Presented) A light emitting device comprising:
 - a light emitting element and a first transistor and a second transistor each for controlling current to be supplied to the light emitting element, which are formed in a pixel,
 - wherein a threshold voltage of the first transistor is higher than a threshold voltage of the second transistor,
 - wherein a channel length of the first transistor is longer than a channel width thereof,
 - wherein a channel length of the second transistor is equal to or shorter than a channel width thereof,
 - wherein gate electrodes of the first transistor and the second transistor are connected to each other,
 - wherein each polarity of the first transistor and the second transistor is p-type,
 - wherein the light emitting element, the first transistor and the second transistor are all connected in series,
 - wherein one of a source region and a drain region of the first transistor is connected to the light emitting element,
 - wherein the other one of the source region and the drain region of the first transistor is connected to one of a source region and a drain region of the second transistor,
 - wherein the first transistor and the second transistor share a same semiconductor island, and
 - wherein the semiconductor island comprises a channel forming region of the first transistor and the second transistor.

2.-5. (Canceled)

6. (Currently Amended) The light emitting device according to ~~any one of Claims 1 to 5~~ claim 1,

wherein a ratio of the channel length to the channel width of the first transistor is equal to or more than 5.

7. (Previously Presented) A device substrate comprising:

a pixel electrode and a first transistor and a second transistor each for controlling current to be supplied to the pixel electrode, which are formed in a pixel,

wherein a threshold voltage of the first transistor is higher than a threshold of the second transistor,

wherein a channel length of the first transistor is longer than a channel width thereof,

wherein a channel length of the second transistor is equal to or shorter than a channel width of the second transistor,

wherein gate electrodes of the first transistor and the second transistor are connected to each other,

wherein each polarity of the first transistor and the second transistor is p-type,

wherein the pixel electrode, the first transistor and the second transistor are all connected in series,

wherein one of a source region and a drain region of the first transistor is connected to the light emitting element,

wherein the other one of the source region and the drain region of the first transistor is connected to one of a source region and a drain region of the second transistor,

wherein the first transistor and the second transistor share a same semiconductor island, and

wherein the semiconductor island comprises a channel forming region of the first transistor and the second transistor.

8.-9. (Canceled)

10. (Currently Amended) The device substrate according to ~~any one of Claims 7 to 9~~ claim 7,

wherein a ratio of the channel length to the channel width of the first transistor is equal to or more than 5.

11. (Previously Presented) A method for driving a light emitting device, comprising the step of:

controlling current to be supplied to a light emitting element by a first transistor and a second transistor,

wherein a threshold voltage of the first transistor is higher than a threshold voltage of the second transistor,

wherein a channel length of the first transistor is longer than a channel width thereof,

wherein a channel length of the second transistor is equal to or shorter than a channel width thereof,

wherein gate electrodes of the first transistor and the second transistor are connected to each other,

wherein each polarity of the first transistor and the second transistor is p-type,

wherein the light emitting element, the first transistor and the second transistor are all connected in series,

wherein one of a source region and a drain region of the first transistor is connected to the light emitting element,

wherein the other one of the source region and the drain region of the first transistor is connected to one of a source region and a drain region of the second transistor,

wherein the first transistor and the second transistor share a same semiconductor island,

wherein the semiconductor island comprises a channel forming region of the first transistor and the second transistor, and

wherein the first transistor operates in a saturated region, and the second transistor operates in a linear region.

12.-13. (Canceled)

14. (Currently Amended) The method for driving the light emitting device according to ~~any one of Claims 11 to 13~~ claim 11,

wherein a ratio of the channel length to the channel width of the first transistor is equal to or more than 5.

15.-22. (Canceled)

23. (Previously Presented) A light emitting device comprising:

a light emitting element and a first transistor and a second transistor each for controlling current to be supplied to the light emitting element, which are formed in a pixel,

wherein a channel length of the first transistor is longer than a channel width thereof,

wherein a channel length of the second transistor is equal to or shorter than a channel width thereof,

wherein gate electrodes of the first transistor and the second transistor are connected to each other,

wherein the first transistor and the second transistor have the same polarity,
wherein the light emitting element, the first transistor and the second transistor are all connected in series,

wherein one of a source region and a drain region of the first transistor is connected to the light emitting element,

wherein the other one of the source region and the drain region of the first transistor is connected to one of a source region and a drain region of the second transistor,

wherein the first transistor and the second transistor share a same semiconductor island, and

wherein the semiconductor island comprises a channel forming region of the first transistor and the second transistor.

24. (Previously Presented) A device substrate comprising:

a pixel electrode and a first transistor and a second transistor each for controlling current to be supplied to the pixel electrode, which are formed in a pixel,

wherein a channel length of the first transistor is longer than a channel width thereof,

wherein a channel length of the second transistor is equal to or shorter than a channel width of the second transistor,

wherein gate electrodes of the first transistor and the second transistor are connected to each other,

wherein the first transistor and the second transistor have the same polarity,

wherein the pixel electrode, the first transistor and the second transistor are all connected in series,

wherein one of a source region and a drain region of the first transistor is connected to the light emitting element,

wherein the other one of the source region and the drain region of the first transistor is connected to one of a source region and a drain region of the second transistor,

wherein the first transistor and the second transistor share a same semiconductor island, and

wherein the semiconductor island comprises a channel forming region of the first transistor and the second transistor.

25. (Previously Presented) A method for driving a light emitting device, comprising the step of:

controlling current to be supplied to a light emitting element by a first transistor and a second transistor,

wherein a channel length of the first transistor is longer than a channel width thereof,

wherein a channel length of the second transistor is equal to or shorter than a channel width thereof,

wherein gate electrodes of the first transistor and the second transistor are connected to each other,

wherein the first transistor and the second transistor have the same polarity,

wherein the light emitting element, the first transistor and the second transistor are all connected in series,

wherein one of a source region and a drain region of the first transistor is connected to the light emitting element, and

wherein the other one of the source region and the drain region of the first transistor is connected to one of a source region and a drain region of the second transistor,

wherein the first transistor and the second transistor share a same semiconductor island,

wherein the semiconductor island comprises a channel forming region of the first transistor and the second transistor, and

wherein the first transistor operates in a saturated region, and the second transistor operates in a linear region.

26. (Previously Presented) The light emitting device according to claim 1, further comprising a third transistor,

wherein a first electrode of the third transistor is electrically connected to a signal line and a second electrode of the third transistor is electrically connected to the gate electrodes of the first transistor and the second transistor.

27. (Previously Presented) The device substrate according to claim 7, further comprising a third transistor,

wherein a first electrode of the third transistor is electrically connected to a signal line and a second electrode of the third transistor is electrically connected to the gate electrodes of the first transistor and the second transistor.

28. (Previously Presented) The method for driving the light emitting device according to claim 11, further comprising a third transistor,

wherein a first electrode of the third transistor is electrically connected to a signal line and a second electrode of the third transistor is electrically connected to the gate electrodes of the first transistor and the second transistor.

29. (Previously Presented) The light emitting device according to claim 23, further comprising a third transistor,

wherein a first electrode of the third transistor is electrically connected to a signal line and a second electrode of the third transistor is electrically connected to the gate electrodes of the first transistor and the second transistor.

30. (Previously Presented) The device substrate according to claim 24, further comprising a third transistor,

wherein a first electrode of the third transistor is electrically connected to a signal line and a second electrode of the third transistor is electrically connected to the gate electrodes of the first transistor and the second transistor.

31. (Previously Presented) The method for driving the light emitting device according to claim 25, further comprising a third transistor,

wherein a first electrode of the third transistor is electrically connected to a signal line and a second electrode of the third transistor is electrically connected to the gate electrodes of the first transistor and the second transistor.

32.-37. (Canceled)